

Customer No.: 31561
Application No.: 10/710,199
Docket No.: 13875-US-PA-X

To the Specification:

Please amend the title into "MOS TRANSISTOR ~~AND FABRICATION THEREOF~~
HAVING A WORK-FUNCTION DOMINATING LAYER".

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Please amend the abstract as the following paragraph:

A MOS transistor including a substrate, a gate dielectric layer on the substrate, a stacked gate on the gate dielectric layer, and a source/drain in the substrate beside the stacked gate is provided. In particular, the stacked gate includes, from bottom to top, a first barrier layer, an interlayer, a work-function-dominating layer, a second barrier layer and a poly-Si layer, wherein the work-function-dominating layer includes a metallic material. A method for fabricating a MOS transistor is described. A gate dielectric layer, a first barrier layer, an interlayer, a work-function-dominating layer, a second barrier layer and a poly-Si layer are sequentially formed on a substrate. The interlayer is capable of adjusting the work function of the work-function-dominating layer and wetting the surface of the first barrier layer. The above layers are then patterned into a gate, and a source/drain is formed in the substrate beside the gate.

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